ON Semiconductor

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Quad 2-Input OR Gate with LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT32A is identical in pinout to the LS32. The device inputs are compatible with Standard CMOS or LSTTL outputs.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 V to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 48 FETs or 12 Equivalent Gates
- These are Pb-Free Devices

Pinout: 14-Lead Packages (Top View)

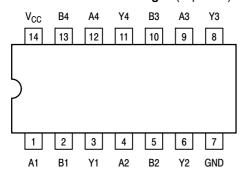


Figure 1. Pinout

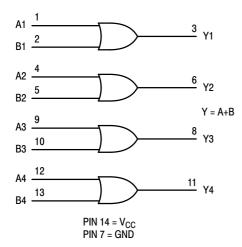


Figure 2. Logic Diagram



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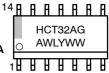
http://onsemi.com

MARKING DIAGRAMS





SOIC-14 D SUFFIX CASE 751A



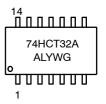


TSSOP-14 DT SUFFIX CASE 948G





SOEIAJ-14 F SUFFIX CASE 965



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

Inputs		Output
А В		Y
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V _{CC} +0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} +0.5	V
l _{in}	DC Input Current, per Pin	±20	mA
l _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation in Still Air, Plastic DIP [†] SOIC Package [†] TSSOP Package [†]	750 500 450	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)			6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			V _{CC}	V
T _A	Operating Temperature, All Package Types		- 55	+125	°C
t _r , t _f	(Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

DC CHARACTERISTICS (Voltages Referenced to GND)

			Vcc	Guaranteed Limit			
Symbol	Parameter	Condition	v	-55 to 25°C	≤ 85°C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1V$ or V_{CC} -0.1V $ I_{out} \le 20\mu A$	4.5 to 5.5	2.0	2.0	2.0	V
V _{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 V$ or $V_{CC} - 0.1 V$ $ I_{out} \le 20 \mu A$	4.5 to 5.5	0.8	0.8	0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad I_{out} \le 4.0 \text{mA}$	4.5	3.98	3.84	3.70	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad I_{out} \le 4.0 \text{mA}$	4.5	0.26	0.33	0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5	±0.1	±1.0	±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0\mu A$	5.5	1.0	10	40	μΑ

AC CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns, V_{CC} = 5.0 V \pm 10%)

		V _{CC}	Guaranteed Limit			
Symbol	Parameter	v	-55 to 25°C	≤ 85 °C	≤125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	5.0	15	19	22	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 2)	5.0	15	19	22	ns
C _{in}	Maximum Input Capacitance		10	10	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V, V _{EE} = 0 V	
C_{PD}	Power Dissipation Capacitance (Per Buffer)*	20	pF

^{*}Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

ORDERING INFORMATION

Device	Package	Shipping †
MC74HCT32ANG	PDIP-14 (Pb-Free)	25 Units / Rail
MC74HCT32ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HCT32ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74HCT32ADTR2G	TSSOP-14*	
MC74HCT32AFELG	SOEIAJ-14 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb-Free.

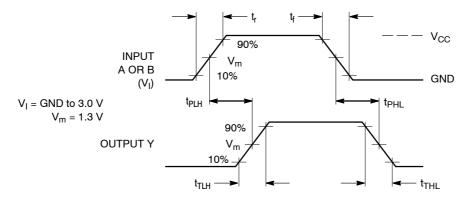
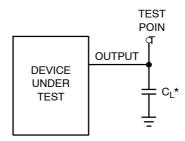


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

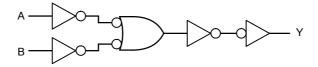
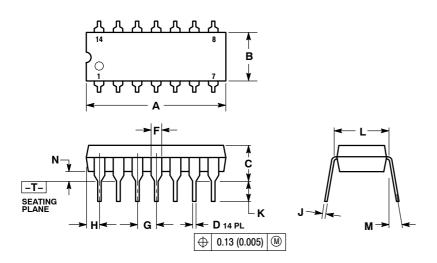


Figure 5. Expanded Logic Diagram (1/4 of the Device)

PACKAGE DIMENSIONS

PDIP-14 CASE 646-06 **ISSUE P**

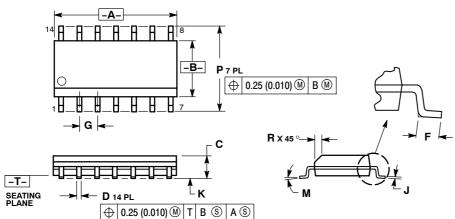


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
М		10 °		10 °
N	0.015	0.039	0.38	1.01

PACKAGE DIMENSIONS

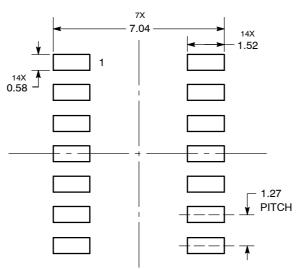
SOIC-14 CASE 751A-03 **ISSUE J**



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.127
 (0.005) TOTAL IN EXCESS OF THE D
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT*

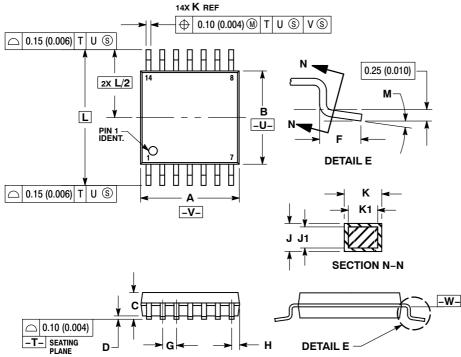


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G-01 **ISSUE B**



NOTES:

- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

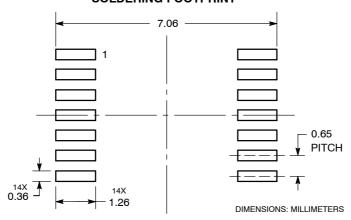
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE

DETE	RMINE) AT DA	TUM PL	ANF -W
T - · -	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.